The RF Line NPN Silicon RF Power Transistor

Designed for 12.5 Volt UHF large—signal amplifier applications in industrial and commercial FM equipment operating to 512 MHz.

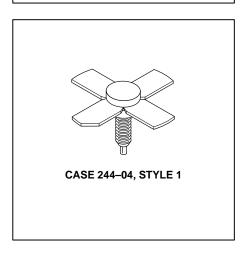
- Specified 12.5 Volt, 512 MHz Characteristics
 Output Power = 10 W
 Gain = 8.0 dB (Typ)
 Efficiency = 65% (Typ)
- Gold Metallized, Emitter Ballasted for Long Life and Reliability
- Capable of 20:1 VSWR Load Mismatch at 16 V Supply Voltage
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MAXIMUM RATINGS

Rating	Symbol	mbol Value	
Collector–Emitter Voltage	VCEO	16.5	Vdc
Collector-Base Voltage	VCBO	38	Vdc
Emitter–Base Voltage	VEBO	4.0	Vdc
Collector Current — Continuous	IC	2.75	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	44 0.25	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Operating Junction Temperature	TJ	200	°C

MRF653

10 W, 512 MHz RF POWER TRANSISTOR NPN SILICON



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	4.0	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS							
Collector–Emitter Breakdown Voltage (I _C = 20 mAdc, I _B = 0)	V(BR)CEO	16.5	_	_	Vdc		
Collector–Emitter Breakdown Voltage (I _C = 20 mAdc, V _{BE} = 0)	V(BR)CES	38	_	_	Vdc		
Emitter–Base Breakdown Voltage (I _E = 5.0 mAdc, I _C = 0)	V(BR)EBO	4.0	_	_	Vdc		
Collector Cutoff Current (V _{CE} = 15 Vdc, V _{BE} = 0)	ICES	_	_	5.0	mAdc		
ON CHARACTERISTICS							
DC Current Gain (I _C = 1.0 Adc, V _{CE} = 5.0 Vdc)	hFE	20	_	120	_		
DYNAMIC CHARACTERISTICS							
Output Capacitance (V _{CB} = 12.5 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	_	22	28	pF		
FUNCTIONAL TESTS							
Common–Emitter Amplifier Power Gain (V _{CC} = 12.5 Vdc, P _{out} = 10 W, f = 512 MHz)	G _{pe}	7.0	8.0	_	dB		
Collector Efficiency (V _{CC} = 12.5 Vdc, P _{out} = 10 W, f = 512 MHz)	ης	55	65	_	%		
Load Mismatch Stress $(V_{CC} = 16 \text{ Vdc}, f = 512 \text{ MHz}, P_{in} (1) = 2.6 \text{ W}, VSWR = 20:1, All Phase Angles})$	Ψ	No Degradation in Output Power					

NOTE:

1. P_{in} = 2.0 dB over the typical input power required for 10 W output power @ 12.5 Vdc.

REV 8



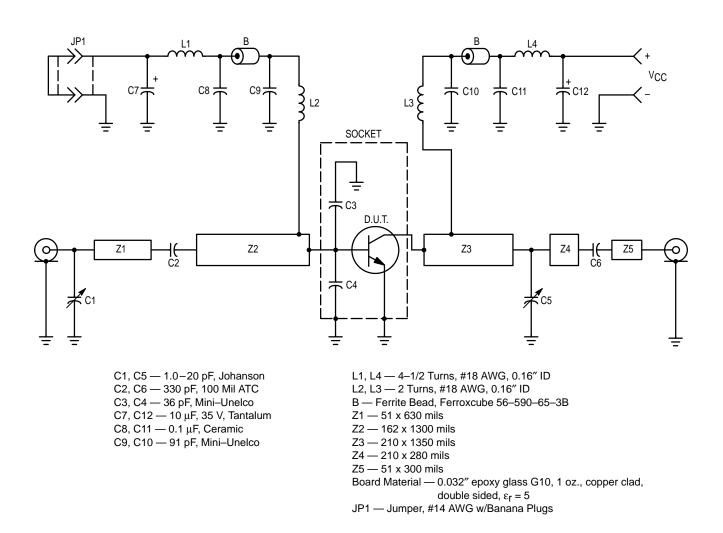


Figure 1. Broadband Test Circuit Schematic

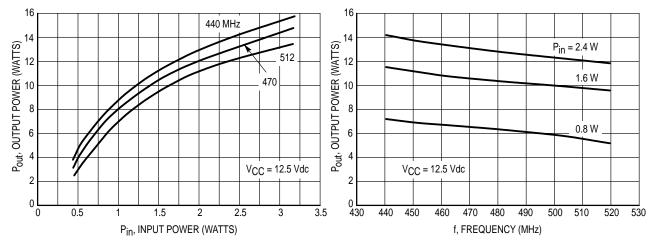


Figure 2. Output Power versus Input Power

Figure 3. Output Power versus Frequency

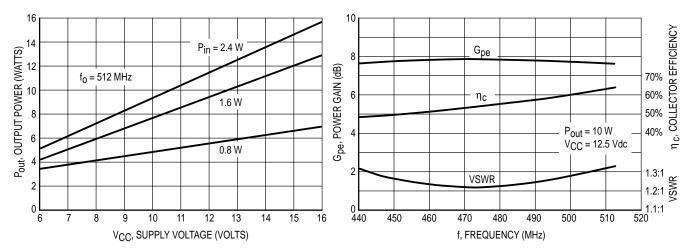


Figure 4. Output Power versus Supply Voltage

Figure 5. Typical Broadband Circuit Performance

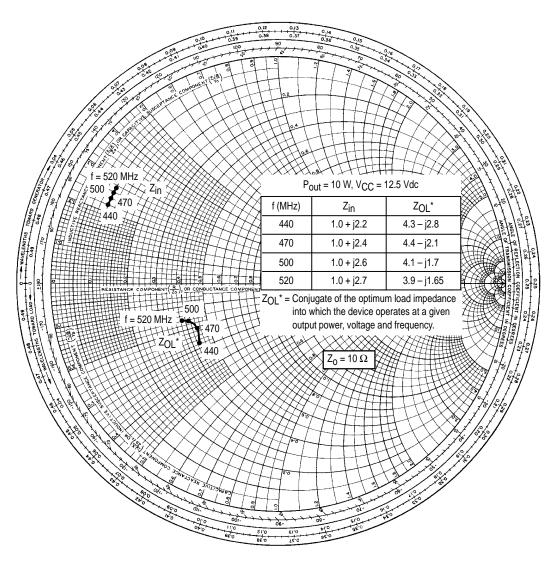
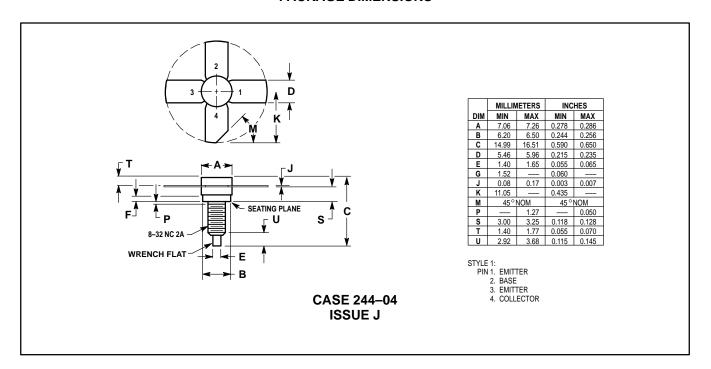


Figure 6. Series Equivalent Input and Output Impedance

PACKAGE DIMENSIONS



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